

NCE N&P-Channel V Complementary MOSFET

Description

The NCE30D2519K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

N channel

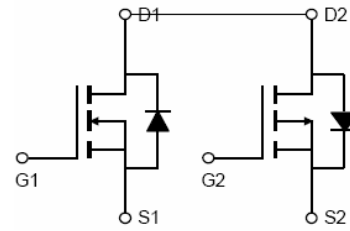
- $V_{DS}=30V, I_D=25A$
- $R_{DS(ON)} < 12m\Omega @ V_{GS}=10V$
- $R_{DS(ON)} < 18m\Omega @ V_{GS}=4.5V$

p channel

- $V_{DS}=-30V, I_D=-19A$
- $R_{DS(ON)} < 35m\Omega @ V_{GS}=-10V$
- $R_{DS(ON)} < 65m\Omega @ V_{GS}=-4.5V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- H-bridge
- Inverters



Schematic diagram



Marking and pin assignment

100% UIS TESTED!

100% ΔV_d s TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
30D2519K	NCE30D2519K	TO-252-4L	-	-	-

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Continuous Drain Current	I_D	25	-19	A
		17.7	-13.4	
Pulsed Drain Current ^(Note 1)	I_{DM}	90	-60	A
Maximum Power Dissipation	P_D	21		W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175		$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	7	$^\circ\text{C/W}$
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N-Channel Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	2.0	3.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =7A	-	8.5	12	mΩ
		V _{GS} =4.5V, I _D =6A	-	11.8	18	mΩ
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =7A	-	29	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	450	-	PF
Output Capacitance	C _{oss}		-	150	-	PF
Reverse Transfer Capacitance	C _{rss}		-	90	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V ,R _L =2.5Ω V _{GS} =10V, R _G =3Ω	-	5	-	nS
Turn-on Rise Time	t _r		-	12	-	nS
Turn-Off Delay Time	t _{d(off)}		-	19	-	nS
Turn-Off Fall Time	t _f		-	6	-	nS
Total Gate Charge	Q _g	V _{DS} =15V, I _D =6A, V _{GS} =10V	-	9.5		nC
Gate-Source Charge	Q _{gs}		-	2.0		nC
Gate-Drain Charge	Q _{gd}		-	1.9		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =25A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	25	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition: T_J=25°C, V_{DD}=30V, V_G=10V, L=0.5mH, R_G=25Ω

N-Channel Typical Electrical and Thermal Characteristics (Curves)

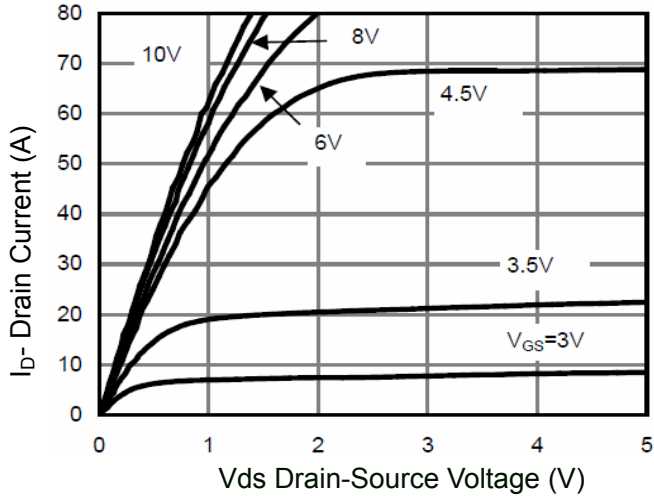


Figure 1 Output Characteristics

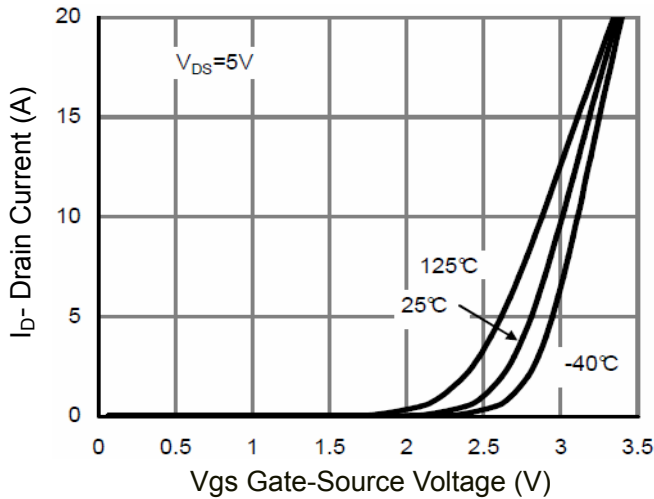


Figure 2 Transfer Characteristics

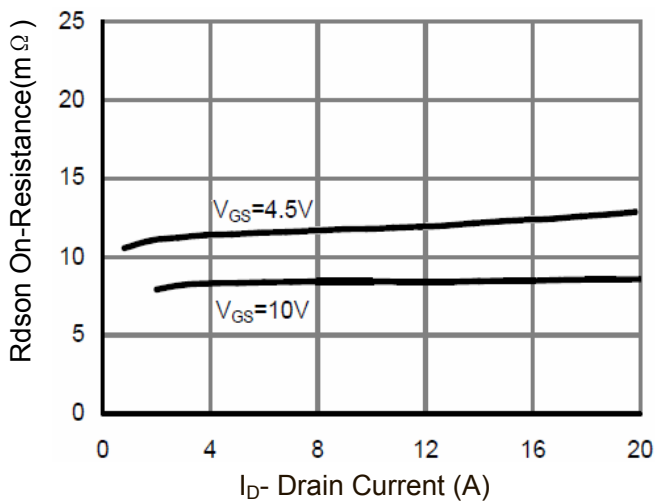


Figure 3 Rdson- Drain Current

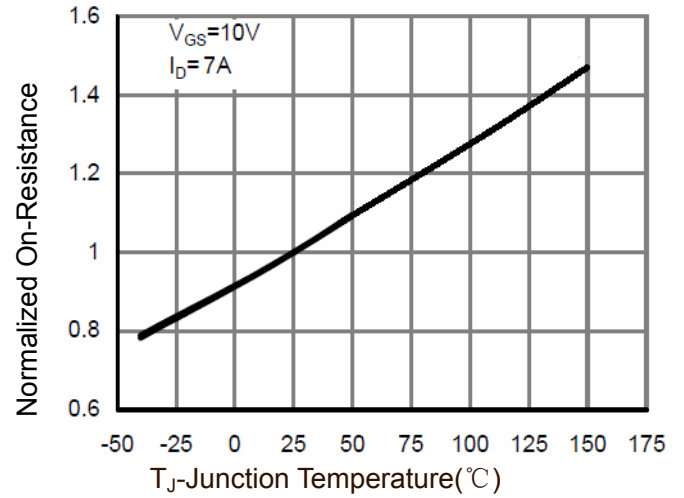


Figure 4 Rdson-Junction Temperature

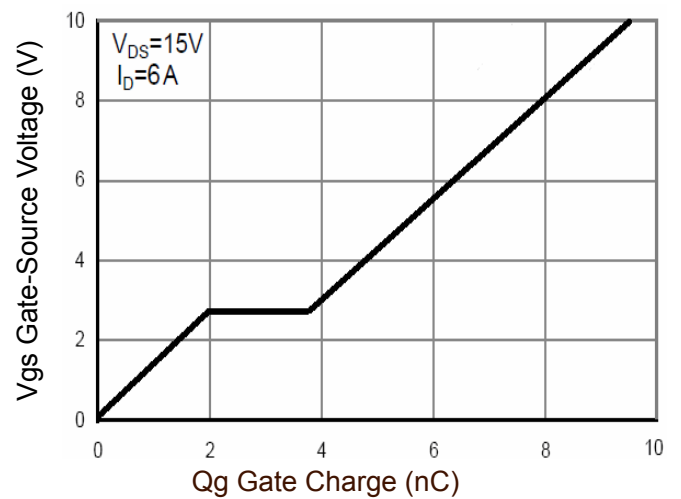


Figure 5 Gate Charge

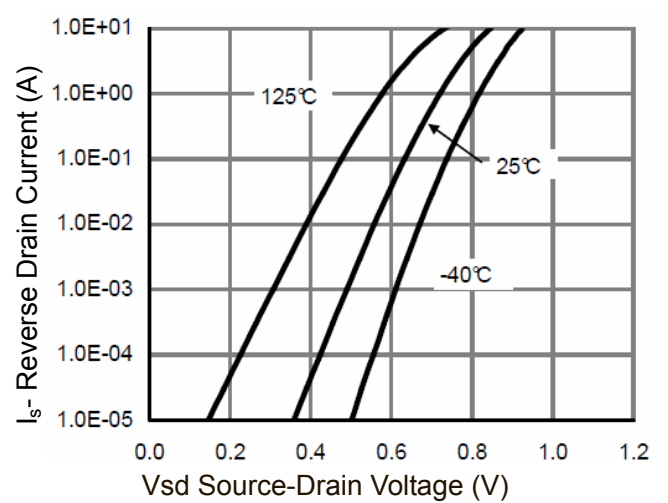


Figure 6 Source- Drain Diode Forward

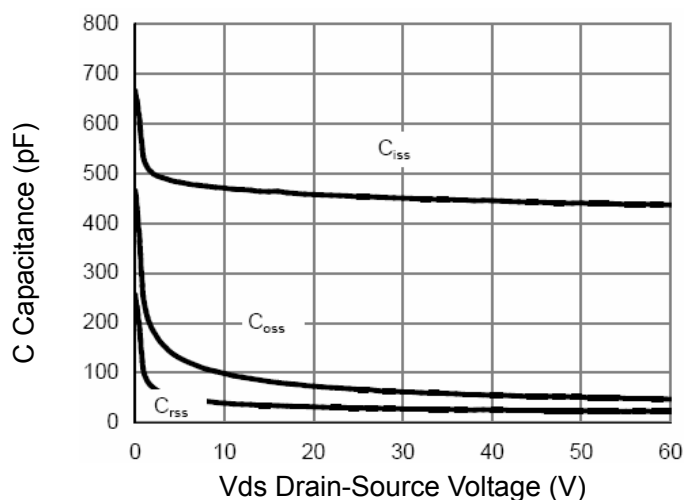


Figure 7 Capacitance vs Vds

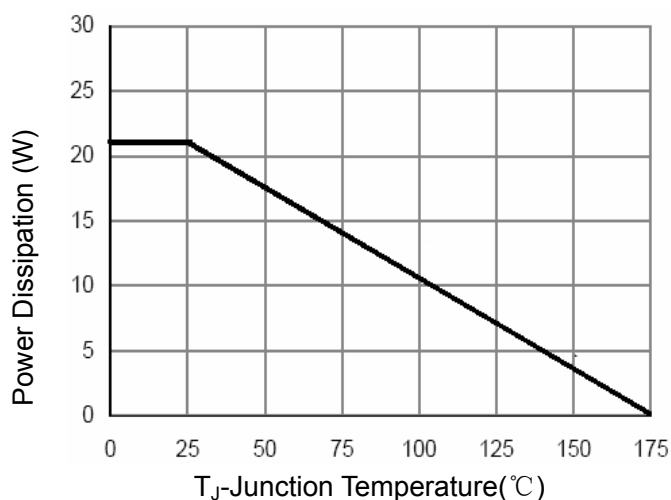


Figure 9 Figure 9 Power De-rating

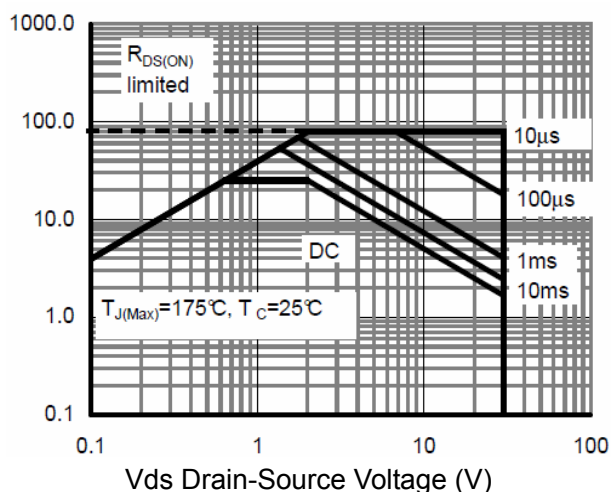


Figure 8 Safe Operation Area

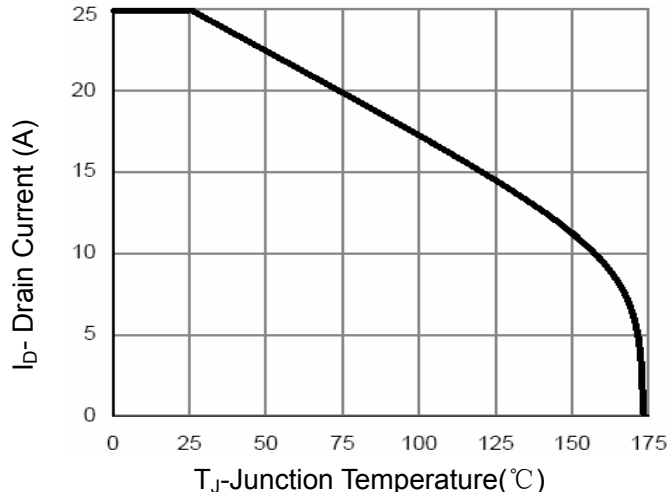


Figure 10 Current De-rating

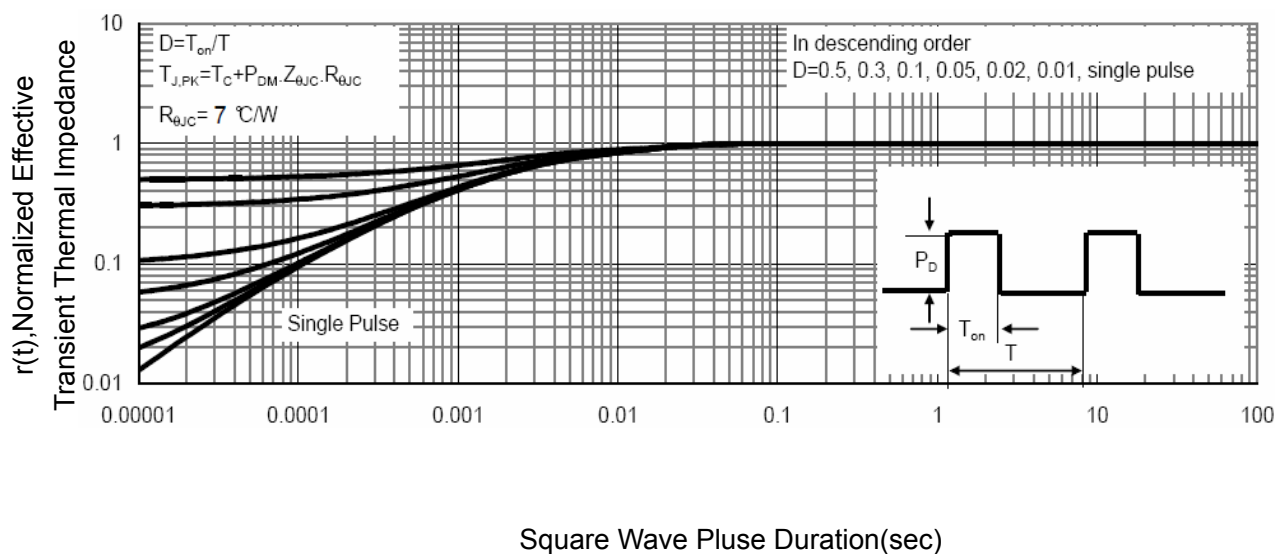


Figure 11 Normalized Maximum Transient Thermal Impedance

P-Channel Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-1.8	-2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-6A	-	28	35	mΩ
		V _{GS} =-4.5V, I _D =-5A		48	65	
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-6A	-	15	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =-30V, V _{GS} =0V, F=1.0MHz	-	920	-	PF
Output Capacitance	C _{oss}		-	140	-	PF
Reverse Transfer Capacitance	C _{rss}		-	90	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V ,R _L =2.5Ω V _{GS} =-10V, R _G =3Ω	-	8	-	nS
Turn-on Rise Time	t _r		-	30	-	nS
Turn-Off Delay Time	t _{d(off)}		-	22	-	nS
Turn-Off Fall Time	t _f		-	26	-	nS
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-6A, V _{GS} =-10V	-	16.2		nC
Gate-Source Charge	Q _{gs}		-	2.9		nC
Gate-Drain Charge	Q _{gd}		-	3.6		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-6A	-		-1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-19	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =-6A di/dt = 100A/μs ^(Note3)	-	23	-	nS
Reverse Recovery Charge	Q _{rr}		-	14	-	nC

P-Channel Typical Electrical and Thermal Characteristics (Curves)

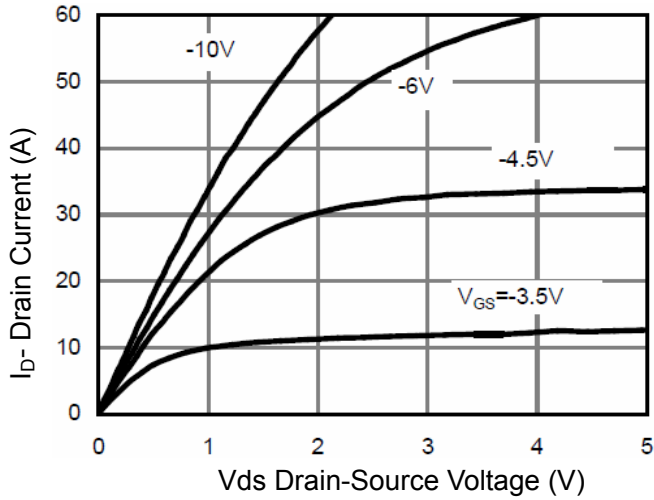


Figure 1 Output Characteristics

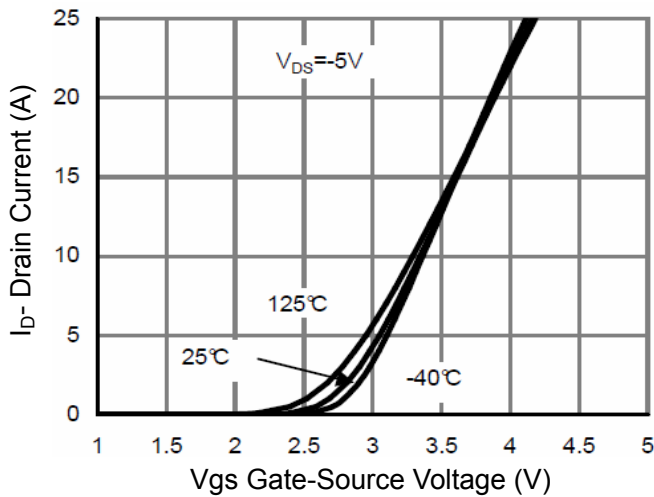


Figure 2 Transfer Characteristics

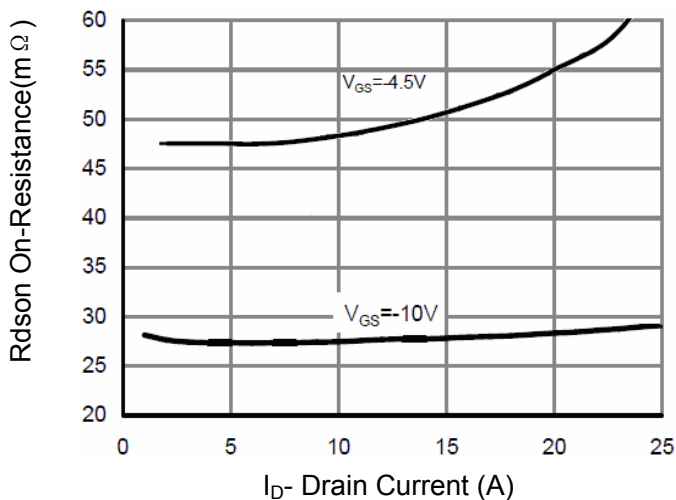


Figure 3 Rdson- Drain Current

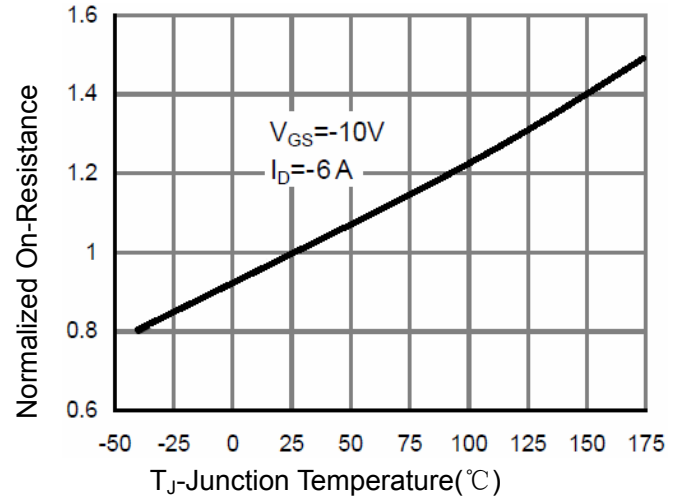


Figure 4 Rdson-Junction Temperature

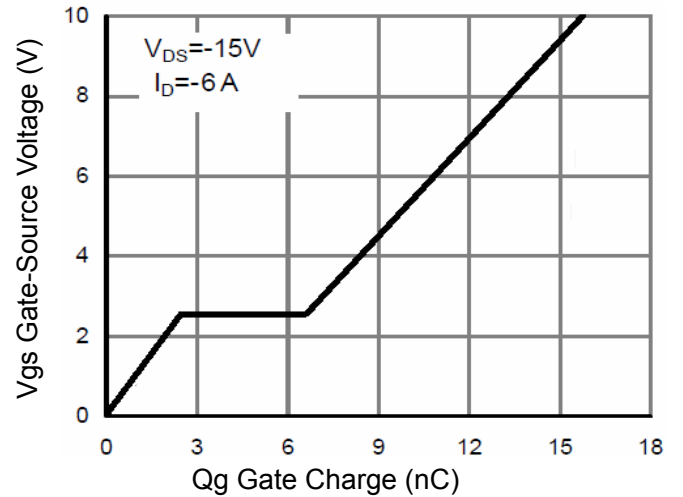


Figure 5 Gate Charge

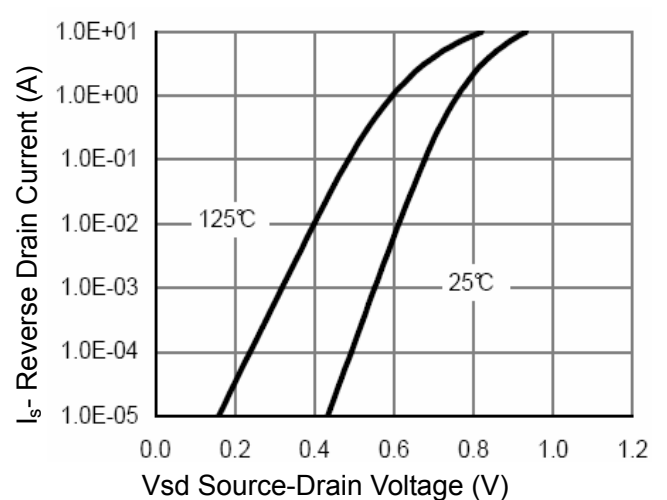


Figure 6 Source- Drain Diode Forward

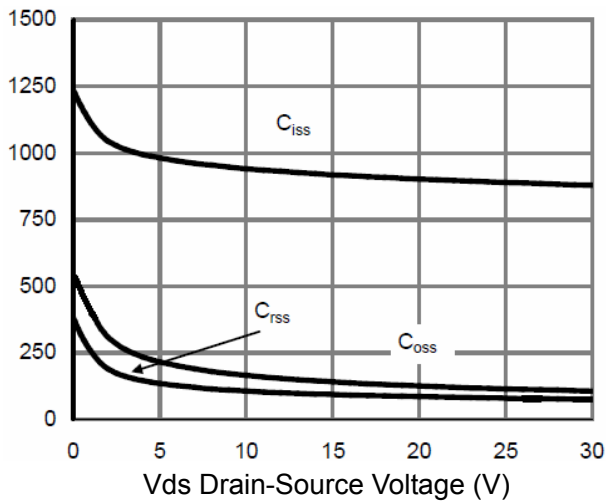


Figure 7 Capacitance vs Vds

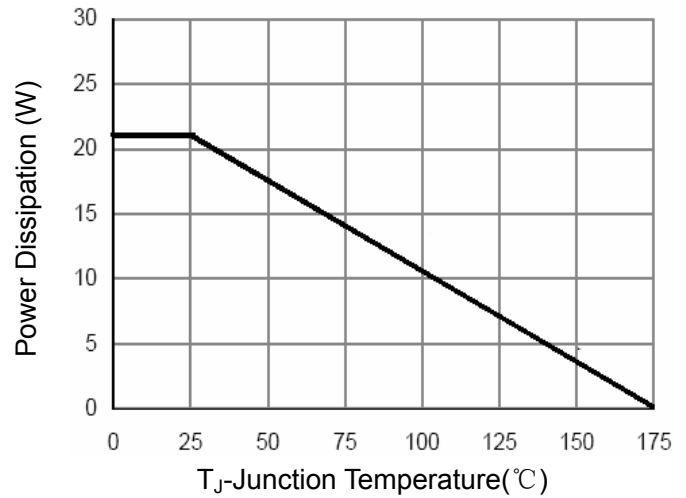


Figure 9 Power De-rating

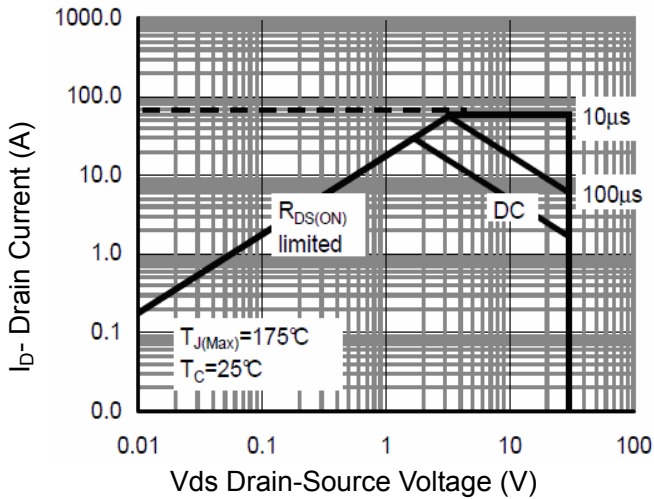


Figure 8 Safe Operation Area

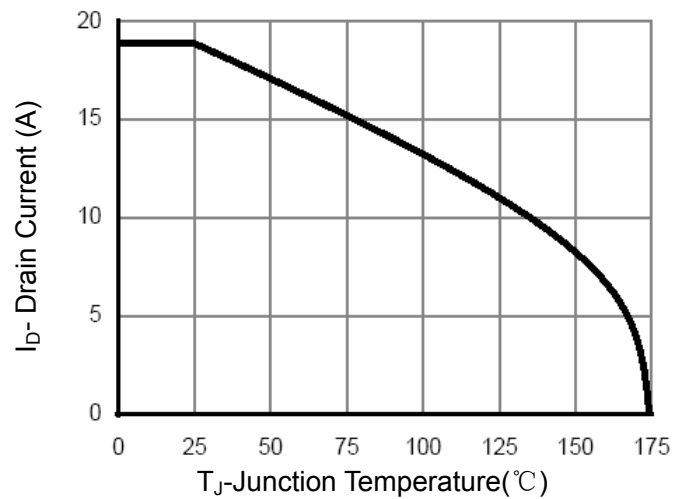


Figure 10 Current De-rating

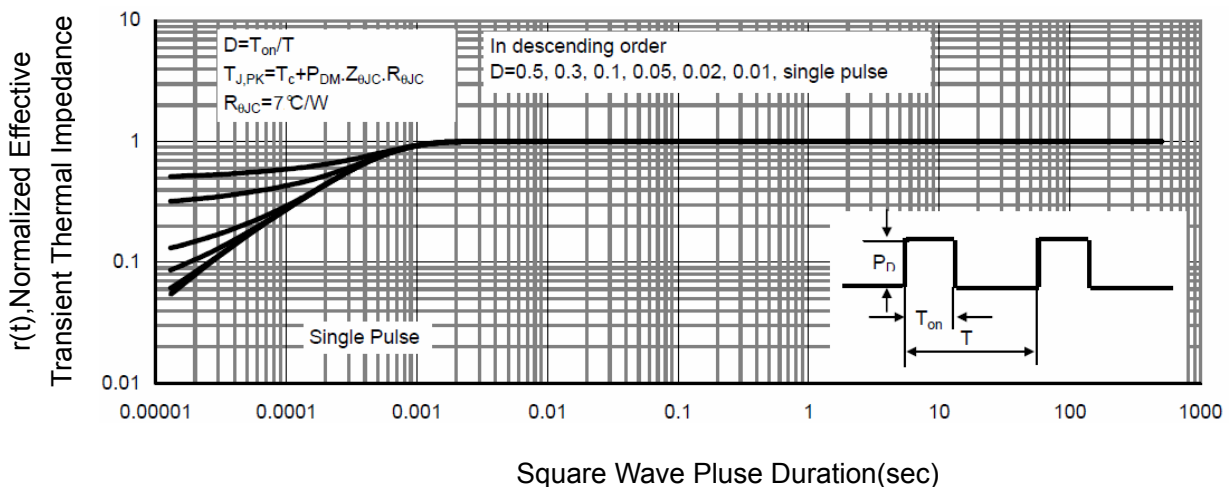
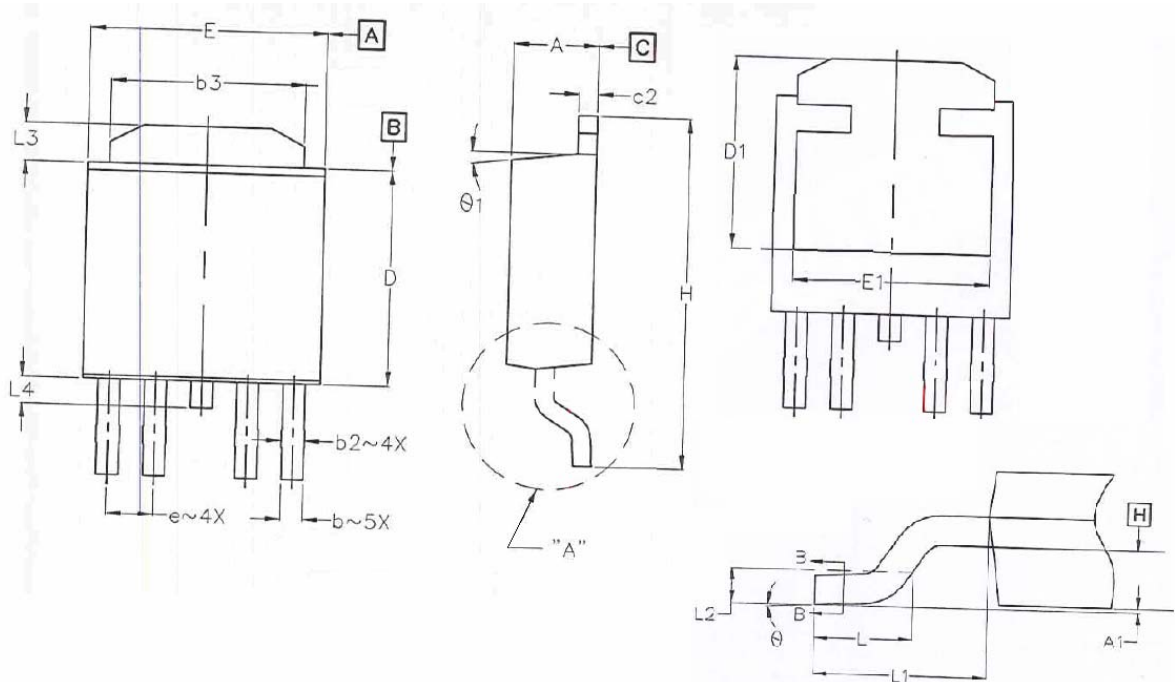


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252-4L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.184	2.387	0.086	0.094
A1	-	0.127	-	0.094
b	0.508	0.711	0.020	0.028
b1	0.508	0.660	0.020	0.026
b2	0.610	0.787	0.024	0.031
b3	4.953	5.461	0.195	0.215
c	0.460	0.610	0.018	0.024
c1	0.410	0.559	0.016	0.022
C2	0.460	12.950	0.498	0.510
D	4.980	5.180	0.196	0.204
D1	2.650	2.950	0.104	0.116
E	7.900	8.100	0.311	0.319
E1	0.000	0.300	0.000	0.012
e	12.900	13.400	0.508	0.528
H	2.850	3.250	0.112	0.128
L	1.397	1.778	0.055	0.070
L1	2.743	BSC	0.108	BSC
L2	0.508	BSC	0.020	BSC
L3	0.889	1.270	0.035	0.050
L4	-	1.015	-	0.040
θ	0°	10°	0°	10°
θ 1	0°	15°	0°	15°

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